

UV-B Sensor

GUVB-S11SD

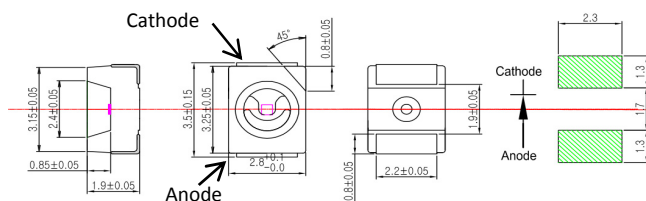


- Features**
- Aluminium Gallium Nitride Based Material
 - Schottky-type Photodiode
 - Photovoltaic Mode Operation
 - Good Visible Blindness
 - High Responsivity & Low Dark Current



Applications UV Index Monitoring

Outline Diagrams and Dimensions



Absolute Maximum Ratings

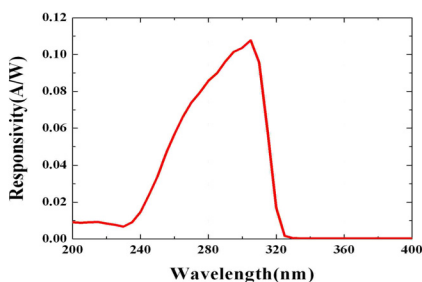
Parameter	Symbol	Min.	Max.	Unit	Remark
Storage Temperature	T _{st}	-40	90	°C	
Operating Temperature	T _{op}	-30	85	°C	
Reverse Voltage	V _{r, max.}		3	V	
Forward Current	I _{f, max.}		1	mA	
Optical Source Power Range	P _{opt}	0.1μ	100m	W/cm ²	UVB Lamp
Soldering Temperature	T _{sol}		260	°C	within 10 sec.

※Notice: apply to us in the case that Optical Source Power is over 100mW/cm²

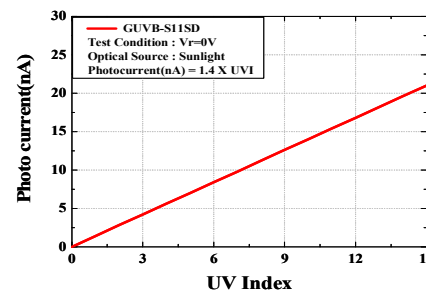
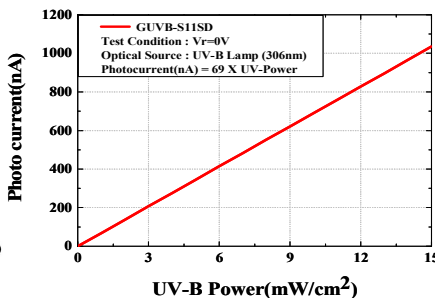
Characteristics (at 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Dark Current	I _d			1	nA	V _r = 0.1 V
Photo Current	I _{ph}	62	69	75	nA	UVB Lamp, 1mW/cm ²
			1.4		nA	1 UVI
Temperature Coefficient	I _{tc}		0.1		%/°C	UVB Lamp
Responsivity	R		0.11		A/W	λ = 300 nm, V _r = 0 V
Spectral Detection Range	λ	240		320	nm	10% of R
Active area			0.076		mm ²	

Responsivity Curve



Photocurrent along UV Power



Caution

ESD can damage the device hence please avoid ESD.